NSN 5962-01-110-8117

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View Online at https://aerobasegroup.com/nsn/5962-01-110-8117

Body Length: 1.290 inches **Body Width:** Between 0.500 inches and 0.610 inches **Body Height:** Between 0.150 inches and 0.210 inches **Maximum Power Dissipation Rating:** 1.0 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+125.0 degrees celsius **End Application:** Training set, electronic warfare, type an/mst-t1 **Features Provided:** Hermetically sealed and monolithic and positive outputs and programmable and w/buffered output **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Dual-in-line **Output Logic Form:** N-type metal oxide-semiconductor logic **Input Circuit Pattern:** 11 input **Case Outline Source And Designator:** D-3 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 6.0 volts power source **Time Rating Per Chacteristic:** 450.00 nanoseconds propagation delay time, low to high level output and 450.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Rom **Memory Capacity:** Unknown **Test Data Document:** 81755-654+5501 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Shelf Life:

24 printed circuit

Terminal Type And Quantity:

N/a

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In	18	<i>(</i>)+	МЛО	201	ure:

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Demilitarization:

Yes - demil/mli

Fiig:

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